Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · Extremely fast switching
- Low reverse recovery current
- · Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power
- · Half-bridge or full-bridge switched-mode
- · Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	arameter Conditions		Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 98$ °C; Fig. 1; Fig. 2	15			А	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; T_{mb} ≤ 98 °C; square-wave pulse	30			А	
I _{FSM} non-repetitive peak		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200			А	
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220		Α		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics		,				
V _F	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 3</u>		-	1.4	2	V
Dynamic	characteristics	'			1		
t _{rr}	reverse recovery time	$I_F = 15 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 4		-	19	-	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	Α	anode		K — A 001aaa020
mb	mb	mounting base; cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BYC15-600 TO-220AC		plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59				

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC15-600	BYC15-600

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	T _{mb} ≤ 100 °C; DC	500	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 98 °C; Fig. 1; Fig. 2	15	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 98 °C$; square-wave pulse	30	Α
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200	Α
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

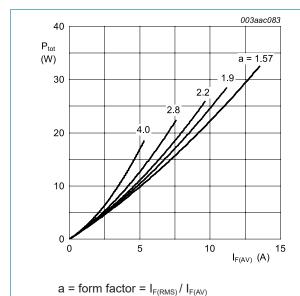
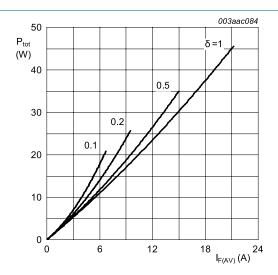


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



 $I_{\text{F(AV)}} = I_{\text{F(RMS)}} \times \sqrt{\delta}$

Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Table 6. Thermal characteristics

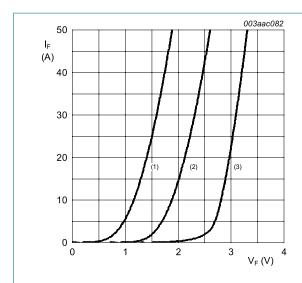
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound	-	-	1.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

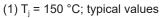
Hyperfast power diode

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	aracteristics					
V _F	forward voltage	I _F = 30A; T _j = 150 °C; <u>Fig. 3</u>	-	1.7	2.3	V
		I _F = 15 A; T _j = 25 °C; <u>Fig. 3</u>	-	1.9	2.9	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 3</u>	-	1.4	2	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	12	200	μA
		V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 4$	-	32	40	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 4$	-	35	55	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 4$	-	19	-	ns
I _{RM}	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 4$	-	9.5	12	А
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 4$	-	3	7.5	А
V _{FR}	forward recovery voltage	$I_F = 15 \text{ A}; \text{ dI}_F/\text{dt} = 100 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; \frac{\text{Fig. 5}}{\text{C}}$	-	8	11	V





⁽²⁾ T_i = 150 °C; maximum values

Fig. 3. Forward current as a function of forward voltage

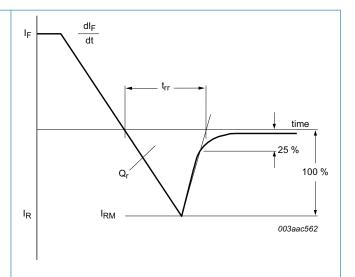
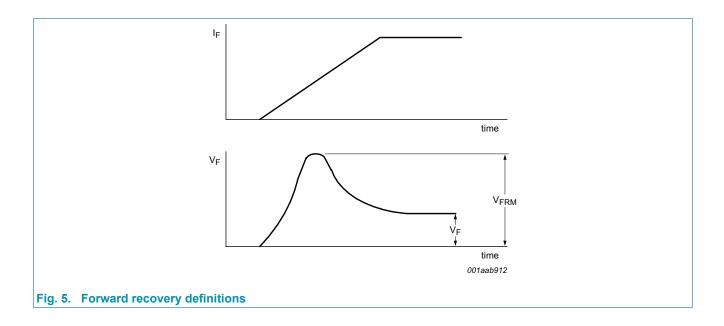


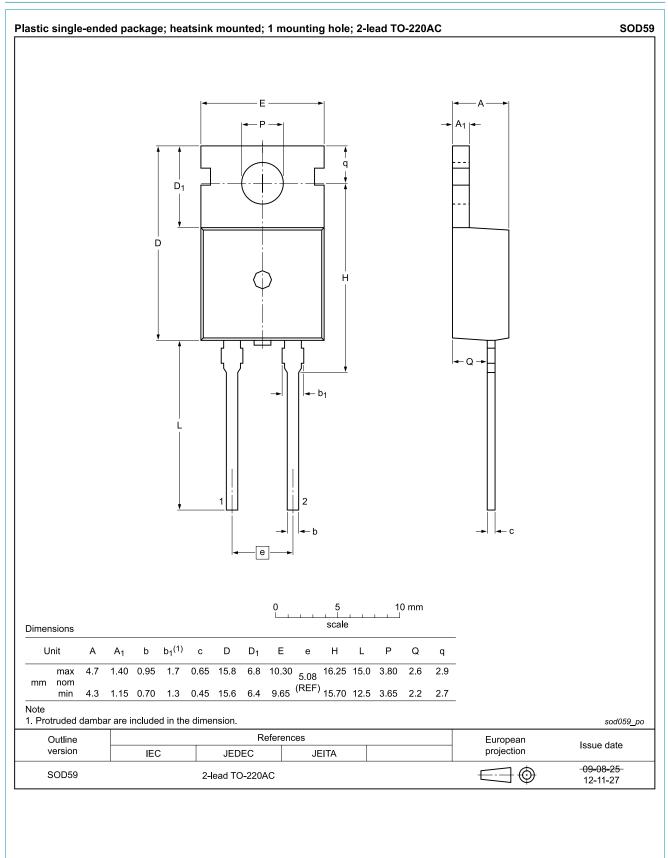
Fig. 4. Reverse recovery definitions; ramp recovery

⁽³⁾ $T_i = 25$ °C; maximum values

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11. Package outline



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12. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC15-600 v.3	20180224	Product data sheet	-	BYC15-600 v.2
Modifications:	Change from NXP version to WeEr	version		
BYC15-600 v.2	20100729	Product data sheet	-	BYC15-600 v.1
Modifications:	Various changes to content.			
BYC15-600 v.1	20071129	Product data sheet	-	-

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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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